

# 2SC5628

Silicon NPN Epitaxial  
High Frequency Amplifier / Oscillator

# HITACHI

ADE-208-979 (Z)

1st. Edition

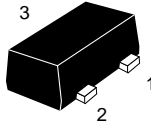
Nov. 2000

## Features

- Super compact package;  
(1.4 × 0.8 × 0.59mm)
- High power gain and low noise figure;  
(PG = 9 dB, NF = 1.1 dB typ, at f = 900 Mhz, V<sub>CE</sub> = 1 V)

## Outline

MFPAK



1. Emitter
2. Base
3. Collector

Note: Marking is "XZ-".

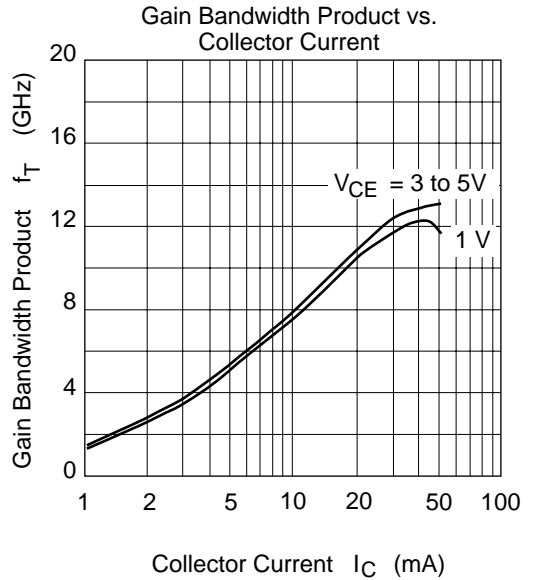
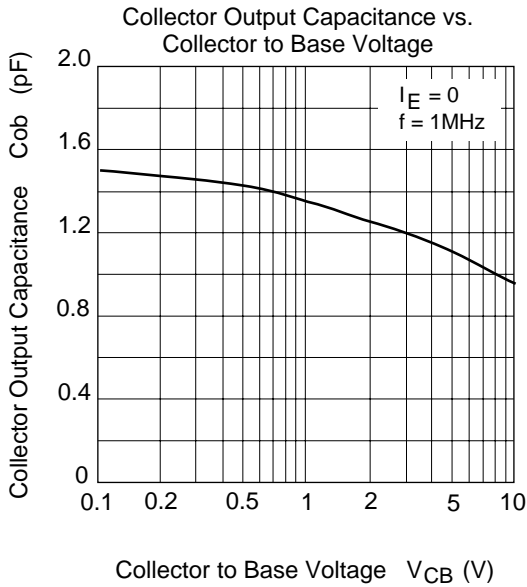
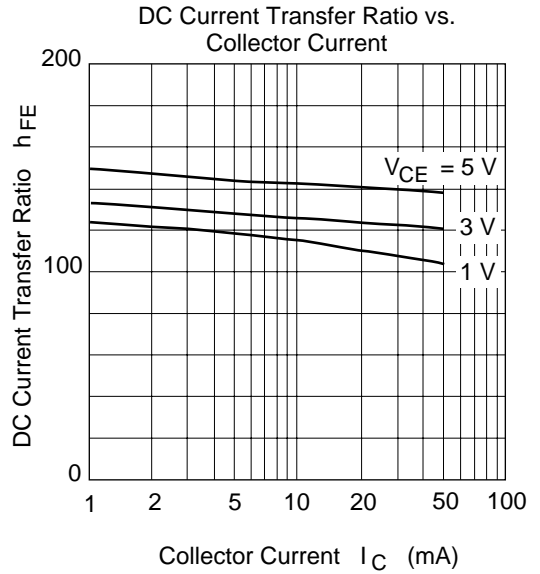
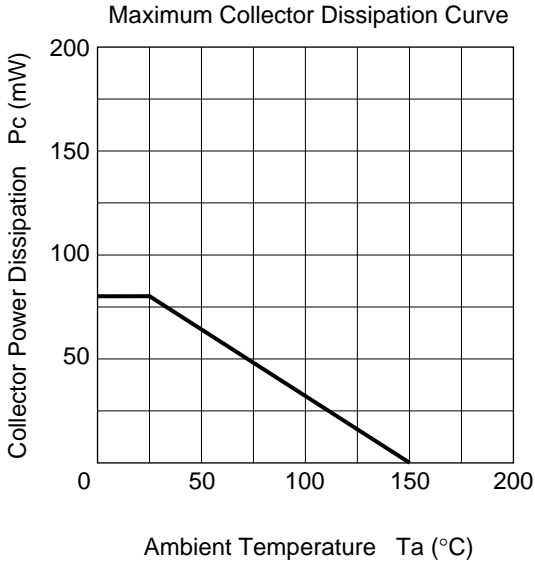
**Absolute Maximum Ratings** ( $T_a = 25^\circ\text{C}$ )

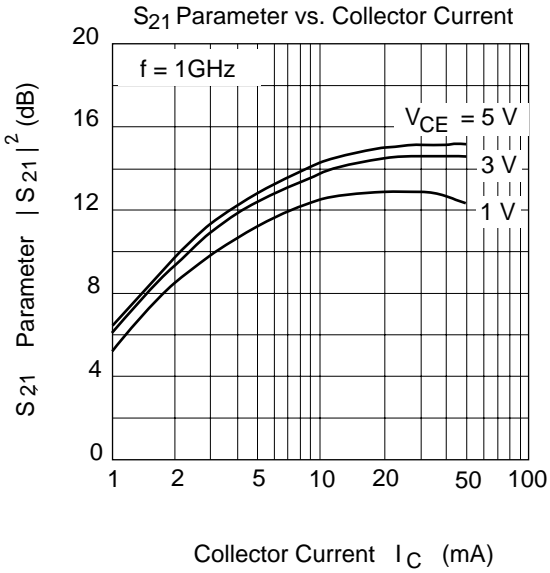
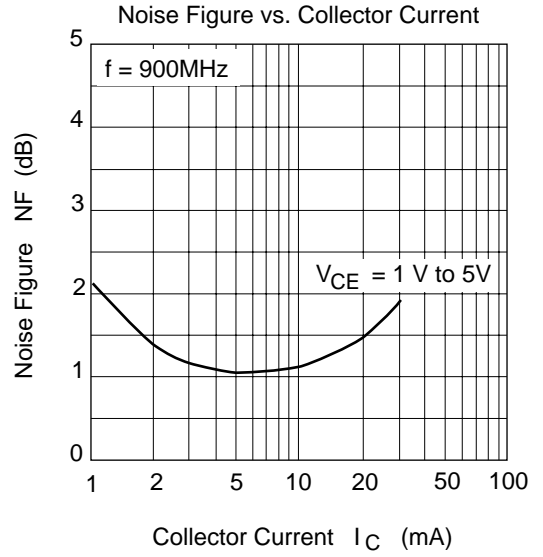
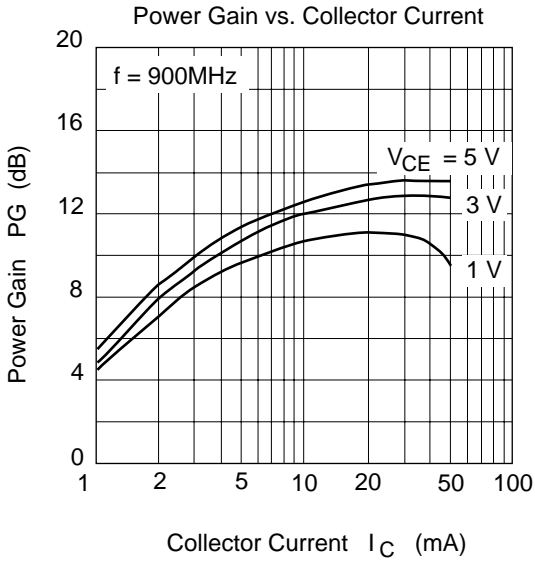
Item	Symbol	Ratings	Unit
Collector to base voltage	$V_{\text{CBO}}$	15	V
Collector to emitter voltage	$V_{\text{CEO}}$	8	V
Emitter to base voltage	$V_{\text{EBO}}$	1.5	V
Collector current	$I_{\text{C}}$	50	mA
Collector power dissipation	$P_{\text{c}}$	80	mW
Junction temperature	$T_{\text{j}}$	150	$^\circ\text{C}$
Storage temperature	$T_{\text{stg}}$	-55 to +150	$^\circ\text{C}$

**Electrical Characteristics** ( $T_a = 25^\circ\text{C}$ )

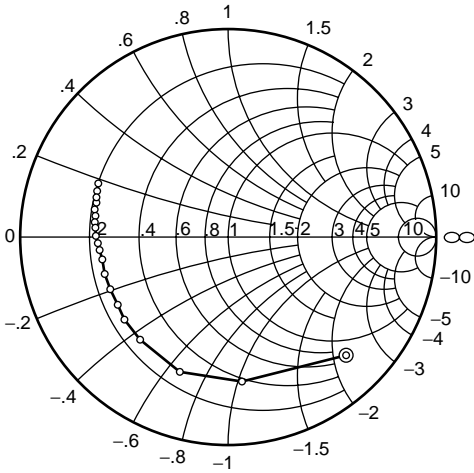
Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Collector to base breakdown voltage	$V_{(\text{BR})\text{CBO}}$	15	—	—	V	$I_{\text{C}} = 10\mu\text{A}$ , $I_{\text{E}} = 0$
Collector cutoff current	$I_{\text{CBO}}$	—	—	1	$\mu\text{A}$	$V_{\text{CB}} = 12\text{V}$ , $I_{\text{E}} = 0$
Collector cutoff current	$I_{\text{CEO}}$	—	—	1	mA	$V_{\text{CE}} = 8\text{V}$ , $R_{\text{BE}} = \infty$
Emitter cutoff current	$I_{\text{EBO}}$	—	—	10	$\mu\text{A}$	$V_{\text{EB}} = 1.5\text{V}$ , $I_{\text{C}} = 0$
DC current transfer ratio	$h_{\text{FE}}$	50	100	160	V	$V_{\text{CE}} = 1\text{V}$ , $I_{\text{C}} = 5\text{mA}$
Collector output capacitance	$C_{\text{ob}}$	—	0.55	0.85	pF	$V_{\text{CB}} = 1\text{V}$ , $I_{\text{E}} = 0$ $f = 1\text{MHz}$
Gain bandwidth product	$f_{\text{T}}$	6	9	—	GHz	$V_{\text{CE}} = 1\text{V}$ , $I_{\text{C}} = 5\text{mA}$
Power gain	PG	11	14	—	dB	$V_{\text{CE}} = 1\text{V}$ , $I_{\text{C}} = 5\text{mA}$ $f = 900\text{MHz}$
Noise figure	NF	—	1.1	2.0	dB	$V_{\text{CE}} = 1\text{V}$ , $I_{\text{C}} = 5\text{mA}$ $f = 900\text{MHz}$

Main Characteristics





S11 Parameter vs. Frequency

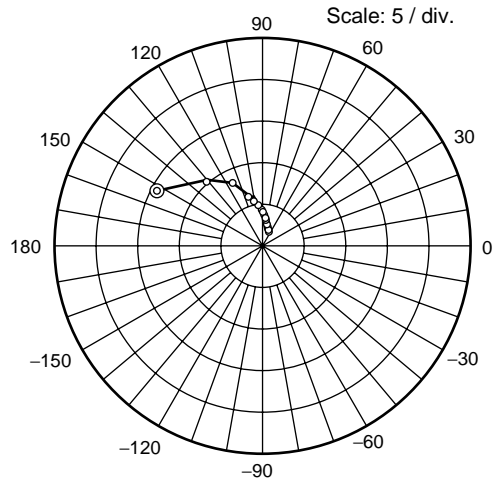


Condition :  $V_{CE} = 1\text{ V}$ ,  $I_C = 5\text{ mA}$

100 to 2000 MHz (100 MHz step)

⊙—○

S21 Parameter vs. Frequency

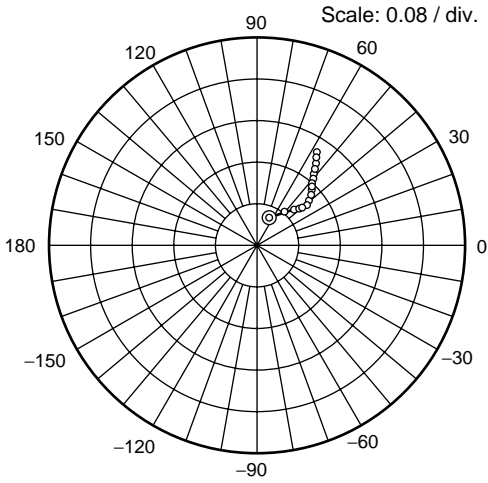


Condition :  $V_{CE} = 1\text{ V}$ ,  $I_C = 5\text{ mA}$

100 to 2000 MHz (100 MHz step)

⊙—○

S12 Parameter vs. Frequency

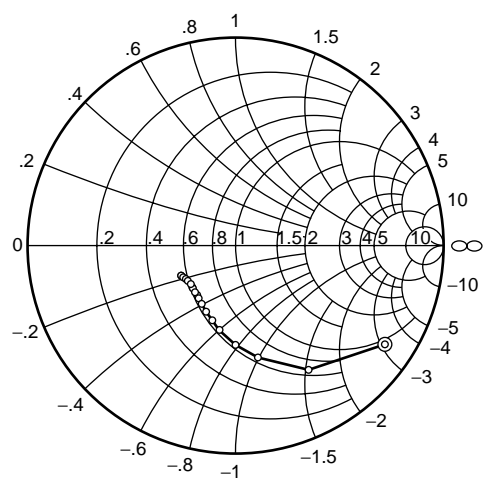


Condition :  $V_{CE} = 1\text{ V}$ ,  $I_C = 5\text{ mA}$

100 to 2000 MHz (100 MHz step)

⊙—○

S22 Parameter vs. Frequency

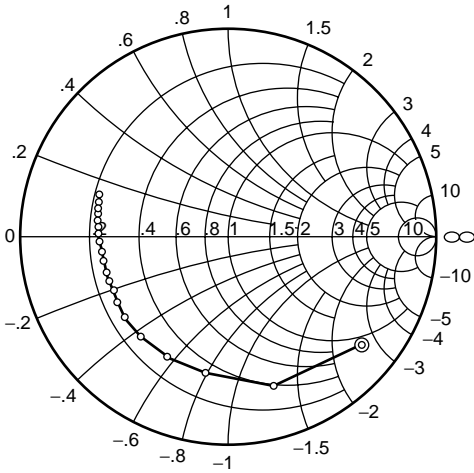


Condition :  $V_{CE} = 1\text{ V}$ ,  $I_C = 5\text{ mA}$

100 to 2000 MHz (100 MHz step)

⊙—○

S11 Parameter vs. Frequency

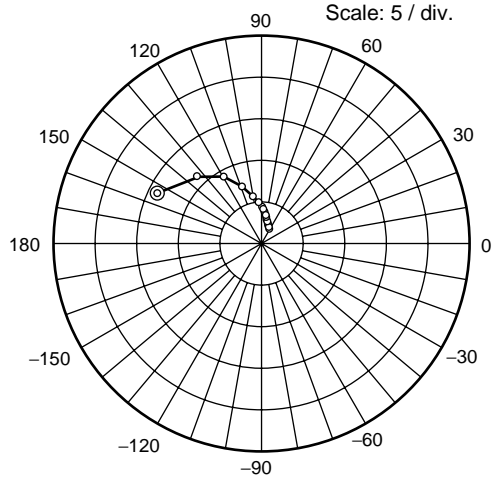


Condition :  $V_{CE} = 3\text{ V}$  ,  $I_C = 5\text{ mA}$

100 to 2000 MHz (100 MHz step)



S21 Parameter vs. Frequency

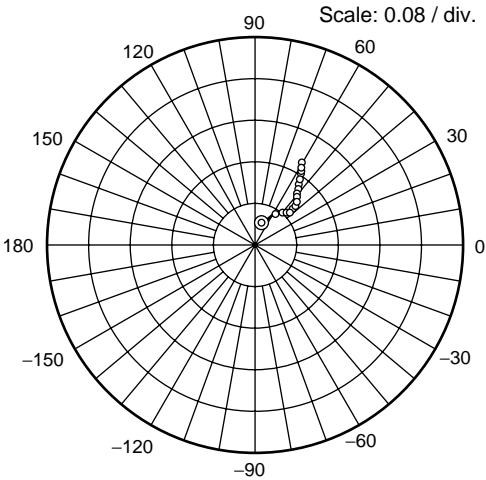


Condition :  $V_{CE} = 3\text{ V}$  ,  $I_C = 5\text{ mA}$

100 to 2000 MHz (100 MHz step)



S12 Parameter vs. Frequency

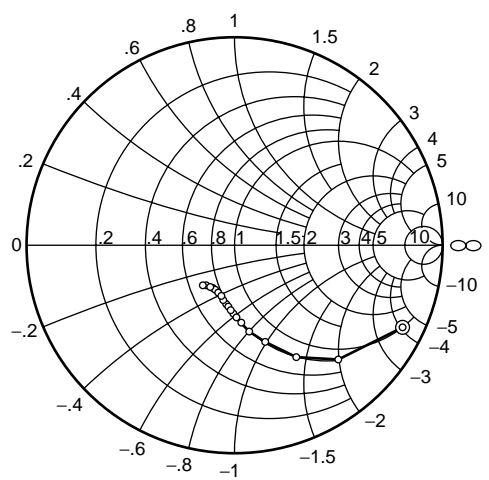


Condition :  $V_{CE} = 3\text{ V}$  ,  $I_C = 5\text{ mA}$

100 to 2000 MHz (100 MHz step)



S22 Parameter vs. Frequency



Condition :  $V_{CE} = 3\text{ V}$  ,  $I_C = 5\text{ mA}$

100 to 2000 MHz (100 MHz step)



Sparameter ( $V_{CE} = 1\text{ V}$ ,  $I_C = 5\text{ mA}$ ,  $Z_o = 50\ \Omega$ )

f (MHz)	S11		S21		S12		S22	
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
100	0.734	-21.4	13.62	163.7	0.0220	78.7	0.956	-13.4
200	0.676	-41.9	12.34	148.7	0.0421	69.3	0.865	-25.5
300	0.598	-59.8	10.79	136.0	0.0572	61.9	0.753	-34.7
400	0.530	-75.6	9.38	126.5	0.0678	57.2	0.652	-41.0
500	0.471	-88.8	8.18	118.9	0.0756	55.0	0.568	-45.4
600	0.429	-100.8	7.19	112.9	0.0821	53.9	0.498	-48.3
700	0.395	-110.8	6.40	107.8	0.0881	53.4	0.442	-50.2
800	0.370	-120.6	5.74	103.5	0.0940	53.4	0.395	-51.7
900	0.349	-130.0	5.20	100.1	0.0990	54.0	0.355	-52.3
1000	0.336	-136.4	4.74	96.9	0.104	54.6	0.323	-52.7
1100	0.332	-144.1	4.39	93.9	0.109	55.5	0.294	-52.9
1200	0.327	-151.6	4.05	91.4	0.115	56.4	0.270	-52.8
1300	0.322	-157.0	3.77	89.1	0.120	57.4	0.250	-52.2
1400	0.325	-162.9	3.54	86.9	0.125	58.0	0.230	-52.6
1500	0.322	-168.0	3.32	84.9	0.130	58.8	0.215	-52.0
1600	0.331	-172.6	3.14	82.7	0.138	59.8	0.200	-51.5
1700	0.338	-177.0	2.97	80.9	0.143	60.3	0.185	-51.5
1800	0.337	179.0	2.84	79.4	0.149	61.5	0.171	-51.2
1900	0.341	175.4	2.71	77.9	0.154	61.7	0.158	-51.1
2000	0.358	170.8	2.59	76.0	0.161	62.4	0.147	-50.9

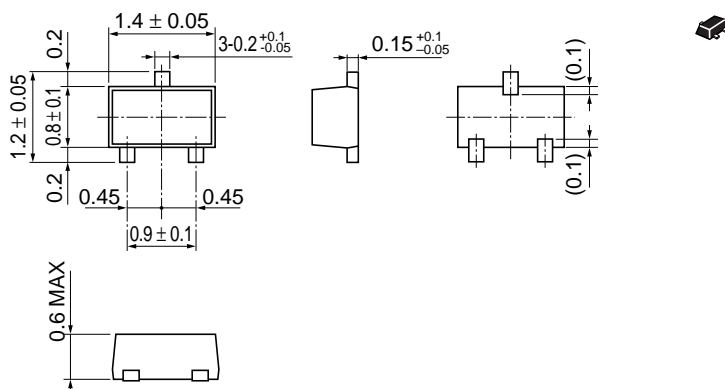
## 2SC5628

Sparameter ( $V_{CE} = 3 \text{ V}$ ,  $I_C = 5 \text{ mA}$ ,  $Z_o = 50 \Omega$ )

f(MHz)	S11		S21		S12		S22	
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
100	0.826	-39.3	14.04	155.5	0.0412	69.9	0.906	-25.8
200	0.746	-74.6	11.47	134.9	0.0700	54.9	0.738	-47.3
300	0.685	-100.5	9.14	121.1	0.0864	46.7	0.591	-61.9
400	0.646	-117.4	7.41	111.9	0.0950	43.0	0.490	-71.9
500	0.627	-130.7	6.19	104.8	0.101	41.3	0.419	-79.9
600	0.617	-141.0	5.27	99.6	0.107	41.3	0.369	-85.7
700	0.606	-149.0	4.61	95.0	0.111	41.6	0.333	-90.7
800	0.598	-155.4	4.09	91.6	0.115	42.5	0.307	-95.3
900	0.605	-161.3	3.67	87.7	0.120	44.3	0.287	-99.0
1000	0.604	-166.1	3.35	84.7	0.124	45.6	0.273	-102.6
1100	0.604	-170.6	3.06	81.8	0.129	46.8	0.262	-106.0
1200	0.607	-174.2	2.83	79.5	0.134	49.0	0.253	-108.8
1300	0.605	-178.2	2.62	77.1	0.139	50.4	0.249	-111.0
1400	0.608	178.9	2.47	74.9	0.145	51.9	0.245	-114.3
1500	0.618	175.5	2.32	72.7	0.152	53.4	0.242	-116.6
1600	0.622	172.4	2.19	70.7	0.157	54.8	0.241	-118.9
1700	0.627	170.0	2.08	68.9	0.164	56.2	0.241	-121.3
1800	0.629	166.9	1.99	66.7	0.171	57.6	0.242	-123.4
1900	0.633	164.3	1.90	65.2	0.177	58.7	0.243	-125.9
2000	0.641	162.3	1.82	63.4	0.186	59.5	0.245	-127.7

## Package Dimensions

Unit: mm



Hitachi Code	MFPAC
JEDEC	—
EIAJ	—
Mass (reference value)	0.0016 g

**Cautions**

1. Hitachi neither warrants nor grants licenses of any rights of Hitachi's or any third party's patent, copyright, trademark, or other intellectual property rights for information contained in this document. Hitachi bears no responsibility for problems that may arise with third party's rights, including intellectual property rights, in connection with use of the information contained in this document.
2. Products and product specifications may be subject to change without notice. Confirm that you have received the latest product standards or specifications before final design, purchase or use.
3. Hitachi makes every attempt to ensure that its products are of high quality and reliability. However, contact Hitachi's sales office before using the product in an application that demands especially high quality and reliability or where its failure or malfunction may directly threaten human life or cause risk of bodily injury, such as aerospace, aeronautics, nuclear power, combustion control, transportation, traffic, safety equipment or medical equipment for life support.
4. Design your application so that the product is used within the ranges guaranteed by Hitachi particularly for maximum rating, operating supply voltage range, heat radiation characteristics, installation conditions and other characteristics. Hitachi bears no responsibility for failure or damage when used beyond the guaranteed ranges. Even within the guaranteed ranges, consider normally foreseeable failure rates or failure modes in semiconductor devices and employ systemic measures such as fail-safes, so that the equipment incorporating Hitachi product does not cause bodily injury, fire or other consequential damage due to operation of the Hitachi product.
5. This product is not designed to be radiation resistant.
6. No one is permitted to reproduce or duplicate, in any form, the whole or part of this document without written approval from Hitachi.
7. Contact Hitachi's sales office for any questions regarding this document or Hitachi semiconductor products.

# HITACHI

**Hitachi, Ltd.**

Semiconductor & Integrated Circuits.  
 Nippon Bldg., 2-6-2, Ôhte-machi, Chiyoda-ku, Tokyo 100-0004, Japan  
 Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

URL	North America	: <a href="http://semiconductor.hitachi.com/">http://semiconductor.hitachi.com/</a>
	Europe	: <a href="http://www.hitachi-eu.com/hel/ecg">http://www.hitachi-eu.com/hel/ecg</a>
	Asia	: <a href="http://sicapac.hitachi-asia.com">http://sicapac.hitachi-asia.com</a>
	Japan	: <a href="http://www.hitachi.co.jp/Sicd/indx.htm">http://www.hitachi.co.jp/Sicd/indx.htm</a>

**For further information write to:**

Hitachi Semiconductor  
 (America) Inc.  
 179 East Tasman Drive,  
 San Jose, CA 95134  
 Tel: <1> (408) 433-1990  
 Fax: <1> (408) 433-0223

Hitachi Europe GmbH  
 Electronic Components Group  
 Dornacher StraÙe 3  
 D-85622 Feldkirchen, Munich  
 Germany  
 Tel: <49> (89) 9 9180-0  
 Fax: <49> (89) 9 29 30 00

Hitachi Europe Ltd.  
 Electronic Components Group.  
 Whitebrook Park  
 Lower Cookham Road  
 Maidenhead  
 Berkshire SL6 8YA, United Kingdom  
 Tel: <44> (1628) 585000  
 Fax: <44> (1628) 585160

Hitachi Asia Ltd.  
 Hitachi Tower  
 16 Collyer Quay #20-00,  
 Singapore 049318  
 Tel: <65>-538-6533/538-8577  
 Fax : <65>-538-6933/538-3877  
 URL : <http://www.hitachi.com.sg>

Hitachi Asia Ltd.  
 (Taipei Branch Office)  
 4/F, No. 167, Tun Hwa North Road,  
 Hung-Kuo Building,  
 Taipei (105), Taiwan  
 Tel: <886>-(2)-2718-3666  
 Fax : <886>-(2)-2718-8180  
 Telex : 23222 HAS-TP  
 URL : <http://www.hitachi.com.tw>

Hitachi Asia (Hong Kong) Ltd.  
 Group III (Electronic Components)  
 7/F., North Tower,  
 World Finance Centre,  
 Harbour City, Canton Road  
 Tsim Sha Tsui, Kowloon,  
 Hong Kong  
 Tel : <852>-(2)-735-9218  
 Fax : <852>-(2)-730-0281  
 URL : <http://www.hitachi.com.hk>

Copyright © Hitachi, Ltd., 2000. All rights reserved. Printed in Japan.  
 Colophon 2.0